July 2025

FSBB20CH60D

Motion SPM® 3 Series

Features

- UL Certified No. E209204 (UL1557)
- 600 V - 20 A 3-Phase IGBT Inverter with Integral Gate Drivers and Protection
- Low-Loss, Short-Circuit Rated IGBTs
- Very Low Thermal Resistance Using Al_2O_3 DBC Substrate
- Built-In Bootstrap Diodes and Dedicated Vs Pins Simplify PCB Layout
- Separate Open-Emitter Pins from Low-Side IGBTs for Three-Phase Current Sensing
- Single-Grounded Power Supply
- LVIC Temperature-Sensing Built-In for Temperature Monitoring
- Isolation Rating: 2500 V_{rms} / 1 min.

Applications

- Motion Control - Home Appliance / Industrial Motor

Related Resources

- *AN-9086 - Motion SPM® 3 Series Users Guide*

General Description

FSBB20CH60D is an advanced Motion SPM® 3 module providing a fully-featured, high-performance inverter output stage for AC Induction, BLDC, and PMSM motors. These modules integrate optimized gate drive of the built-in IGBTs to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockouts, over-current shutdown, thermal monitoring of drive IC, and fault reporting. The built-in, high-speed HVIC requires only a single supply voltage and translates the incoming logic-level gate inputs to the high-voltage, high-current drive signals required to properly drive the module's internal IGBTs. Separate negative IGBT terminals are available for each phase to support the widest variety of control algorithms.

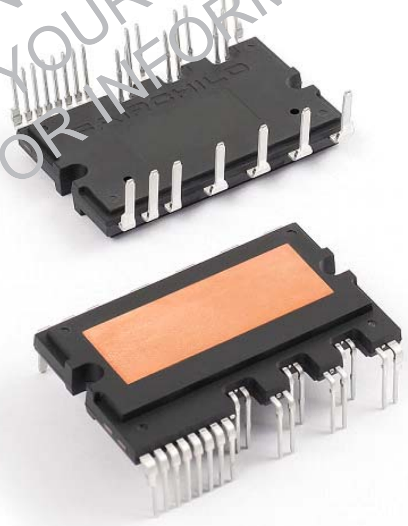


Figure 1. Package Overview

Package Marking and Ordering Information

Device	Device Marking	Package	Packing Type	Quantity
FSBB20CH60D	FSBB20CH60D	SPMCC-027	Rail	10

Integrated Power Functions

- 600 V - 20 A IGBT inverter for three-phase DC / AC power conversion (Please refer to Figure 3)

Integrated Drive, Protection and System Control Functions

- For inverter high-side IGBTs: gate drive circuit, high-voltage isolated high-speed level shifting control circuit Under-Voltage Lock-Out Protection (UVLO)
  Note: Available bootstrap circuit example is given in Figures 5 and 14.
- For inverter low-side IGBTs: gate drive circuit, Short-Circuit Protection (SCP)
  control supply circuit Under-Voltage Lock-Out Protection (UVLO)
- Fault signaling: corresponding to UVLO (low-side supply) and SC faults
- Input interface: active-HIGH interface, works with 3.3 / 5 V logic, Schmitt-trigger input

Pin Configuration

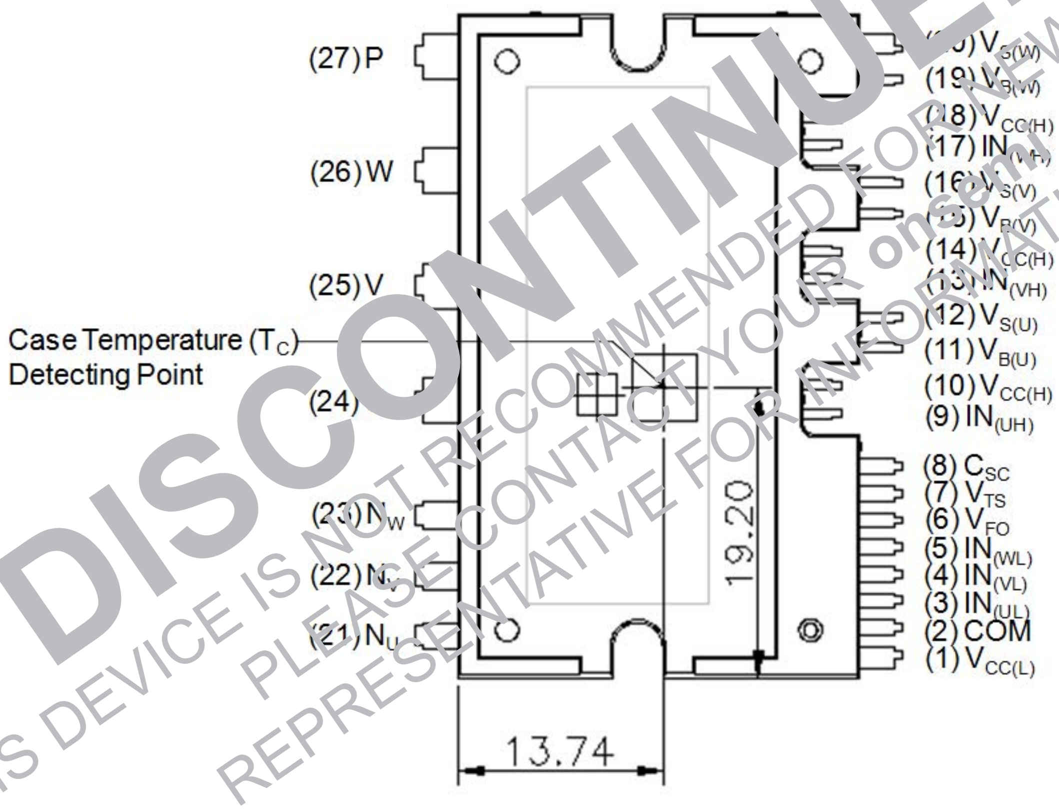


Figure 2. Top View

Pin Descriptions

Pin Number	Pin Name	Pin Description
1	$V_{CC(L)}$	Low-Side Common Bias Voltage for IC and IGBTs Driving
2	COM	Common Supply Ground
3	$IN_{(UL)}$	Signal Input for Low-Side U-Phase
4	$IN_{(VL)}$	Signal Input for Low-Side V-Phase
5	$IN_{(WL)}$	Signal Input for Low-Side W-Phase
6	V_{FO}	Fault Output
7	V_{TS}	Output for LVIC Temperature Sensing Voltage Output
8	C_{SC}	Capacitor (Low-Pass Filter) for Short-Circuit Current Detection Input
9	$IN_{(UH)}$	Signal Input for High-Side U-Phase
10	$V_{CC(H)}$	High-Side Common Bias Voltage for IC and IGBTs Driving
11	$V_{B(U)}$	High-Side Bias Voltage for U-Phase IGBT Driving
12	$V_{S(U)}$	High-Side Bias Voltage Ground for U-Phase IGBT Driving
13	$IN_{(VH)}$	Signal Input for High-Side V-Phase
14	$V_{CC(H)}$	High-Side Common Bias Voltage for IC and IGBTs Driving
15	$V_{B(V)}$	High-Side Bias Voltage for V-Phase IGBT Driving
16	$V_{S(V)}$	High-Side Bias Voltage Ground for V-Phase IGBT Driving
17	$IN_{(WH)}$	Signal Input for High-Side W-Phase
18	$V_{CC(H)}$	High-Side Common Bias Voltage for IC and IGBTs Driving
19	$V_{B(W)}$	High-Side Bias Voltage for W-Phase IGBT Driving
20	$V_{S(W)}$	High-Side Bias Voltage Ground for W-Phase IGBT Driving
21	N_U	Negative DC-Link Input for U-Phase
22	N_V	Negative DC-Link Input for V-Phase
23	N_W	Negative DC-Link Input for W-Phase
24	U	Output for U-Phase
25	V	Output for V-Phase
26	W	Output for W-Phase
27	P	Positive DC-Link Input

Internal Equivalent Circuit and Input/Output Pins

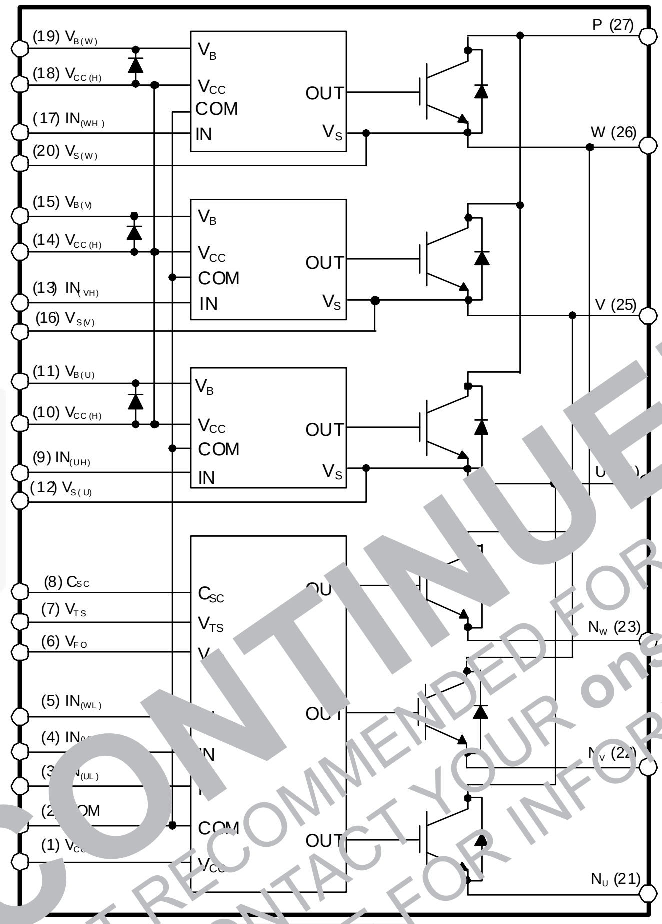


Figure 3. Internal Block Diagram

Notes:

1. Inverter low-side is composed of three IGBTs, freewheeling diodes for each IGBT, and one control IC. It has gate drive and protection functions.
2. Inverter power side is composed of four inverter DC-link input terminals and three inverter output terminals.
3. Inverter high-side is composed of three IGBTs, freewheeling diodes, and three drive ICs for each IGBT.

Absolute Maximum Ratings (T_J = 25°C, Unless Otherwise Specified)

Inverter Part

Symbol	Parameter	Conditions	Rating	Unit
V_{PN}	Supply Voltage	Applied between P - N_U, N_V, N_W	450	V
$V_{PN(Surge)}$	Supply Voltage (Surge)	Applied between P - N_U, N_V, N_W	500	V
V_{CES}	Collector - Emitter Voltage		600	V
$\pm I_C$	Each IGBT Collector Current	T_C = 25°C, $T_J \le$ 150°C (Note 4)	20	A
$\pm I_{CP}$	Each IGBT Collector Current (Peak)	T_C = 25°C, $T_J \le$ 150°C, Under 1 ms Pulse Width (Note 4)	40	A
P_C	Collector Dissipation	T_C = 25°C per One Chip (Note 4)	65	W
T_J	Operating Junction Temperature		-40 ~ 150	°C

Control Part

Symbol	Parameter	Conditions	Rating	Unit
V_{CC}	Control Supply Voltage	Applied between $V_{CC(H)}$, $V_{CC(L)}$ - COM	20	V
V_{BS}	High-Side Control Bias Voltage	Applied between $V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	20	V
V_{IN}	Input Signal Voltage	Applied between $IN_{(UH)}$, $IN_{(VH)}$, $IN_{(WH)}$, $IN_{(UL)}$, $IN_{(VL)}$, $IN_{(WL)}$ - COM	-0.3 ~ V_{CC}+0.3	V
V_{FO}	Fault Output Supply Voltage	Applied between V_{FO} - COM	-0.3 ~ V_{CC}+0.3	V
I_{FO}	Fault Output Current	Sink current at V_{FO} pin	2	mA
V_{SC}	Current Sensing Input Voltage	Applied between C_{SC} - COM	-0.3 ~ V_{CC}+0.3	V

Bootstrap Diode Part

Symbol	Parameter	Conditions	Rating	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage		600	V
I_F	Forward Current	T_C = 25°C, $T_J \le$ 150°C (Note 4)	0.5	A
I_{FP}	Forward Current (Peak)	T_C = 25°C, $T_J \le$ 150°C, Under 1 ms Pulse Width (Note 4)	2.0	A
T_J	Operating Junction Temperature		-40 ~ 150	°C

Total System

Symbol	Parameter	Conditions	Rating	Unit
$V_{PN(PROT)}$	Self Protection Supply Voltage Limit (Short Circuit Protection Capability)	V_{CC} = V_{BS} = 13.5 ~ 16.5 V, T_J = 150°C, Non-repetitive, < 2 μs	400	V
T_C	Module Case Operation Temperature	*See Figure 2*	-40 ~ 125	°C
T_{STG}	Storage Temperature		-40 ~ 125	°C
V_{ISO}	Isolation Voltage	60 Hz, Sinusoidal, AC 1 minute, Connection Pins to Heat Sink Plate	2500	V_{rms}

Thermal Resistance

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$R_{th(j-c)Q}$	Junction to Case Thermal Resistance (Note 5)	Inverter IGBT part (per 1 / 6 module)	-	-	1.90	°C / W
$R_{th(j-c)F}$		Inverter FWD part (per 1 / 6 module)	-	-	2.85	°C / W

Note:

4. These values had been made an acquisition by the calculation considered to design factor.
5. For the measurement point of case temperature (T_C), *please refer to Figure 2.*

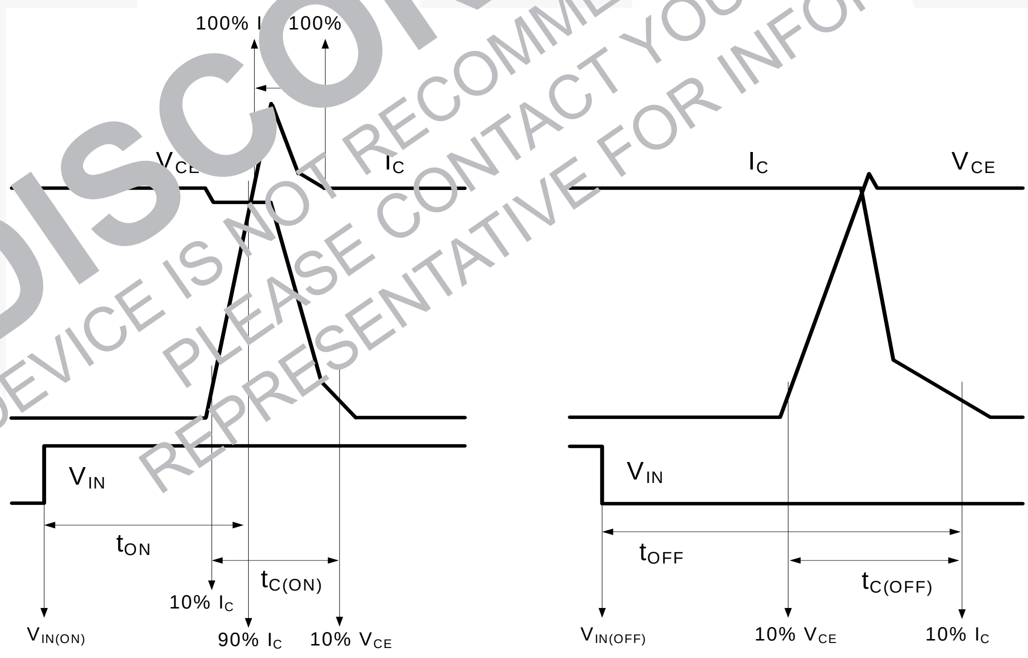
Electrical Characteristics (T_J = 25°C, Unless Otherwise Specified)

Inverter Part

Symbol		Parameter	Conditions		Min.	Typ.	Max.	Unit
$V_{CE(SAT)}$		Collector - Emitter Saturation Voltage	V_{CC} = V_{BS} = 15 V V_{IN} = 5 V	I_C = 20 A, T_J = 25°C	-	-	2.0	V
V_F		FWDi Forward Voltage	V_{IN} = 0 V	I_F = 20 A, T_J = 25°C	-	-	2.2	V
HS	t_{ON}	Switching Times	V_{PN} = 300 V, V_{CC} = 15 V, I_C = 20 A T_J = 25°C V_{IN} = 0 V ↔ 5 V, Inductive Load *See Figure 5* (Note 6)		-	1.0	-	μs
	$t_{C(ON)}$				-	0.4	-	μs
	t_{OFF}				-	0.4	-	μs
	$t_{C(OFF)}$				-	0.1	-	μs
	t_{rr}				-	[illegible]	-	μs
LS	t_{ON}		V_{PN} = 300 V, V_{CC} = 15 V, I_C = 20 A T_J = 25°C V_{IN} = 0 V ↔ 5 V, Inductive Load *See Figure 5* (Note 6)		-	0.8	-	μs
	$t_{C(ON)}$				-	0.3	-	μs
	t_{OFF}				[illegible]	[illegible]	[illegible]	μs
	$t_{C(OFF)}$				-	0.1	-	μs
	t_{rr}				-	0.1	-	μs
I_{CES}		Collector - Emitter Leakage Current	V_{CE} = V_{CES}		-	-	5	mA

Note:

6. t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, *please see Figure 4*.



(a) turn-on **(b) turn-off**

Figure 4. Switching Time Definition

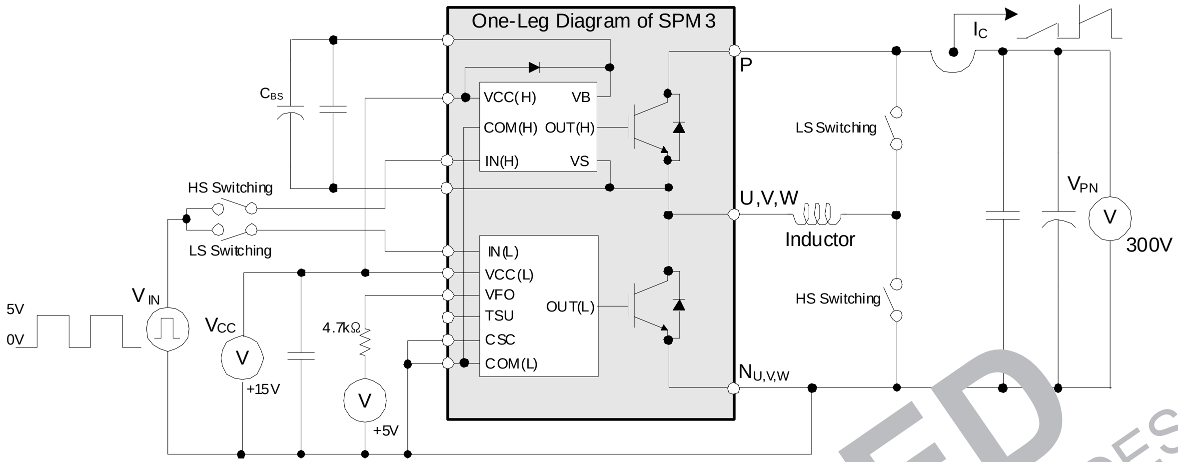


Figure 5. Example Circuit for Switching Test

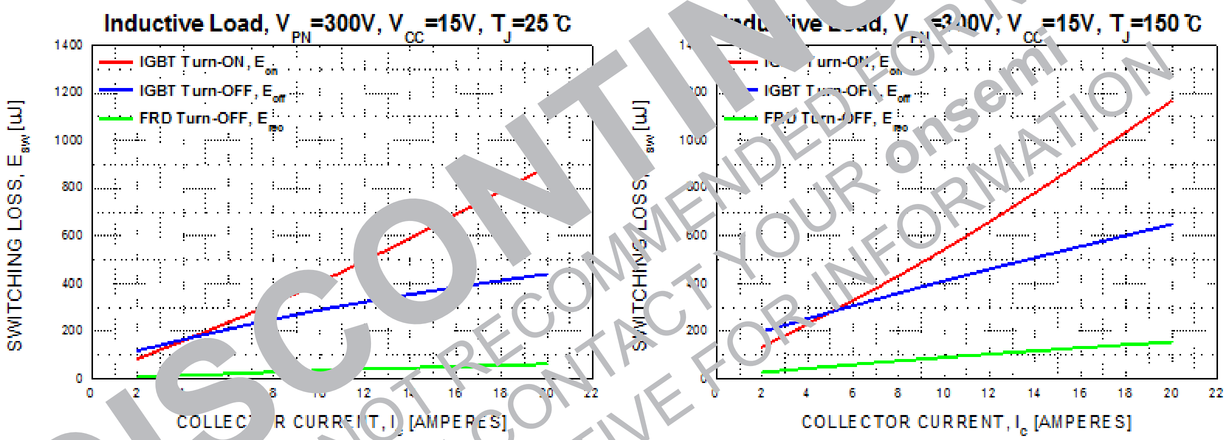


Figure 6. Switching Loss Characteristics

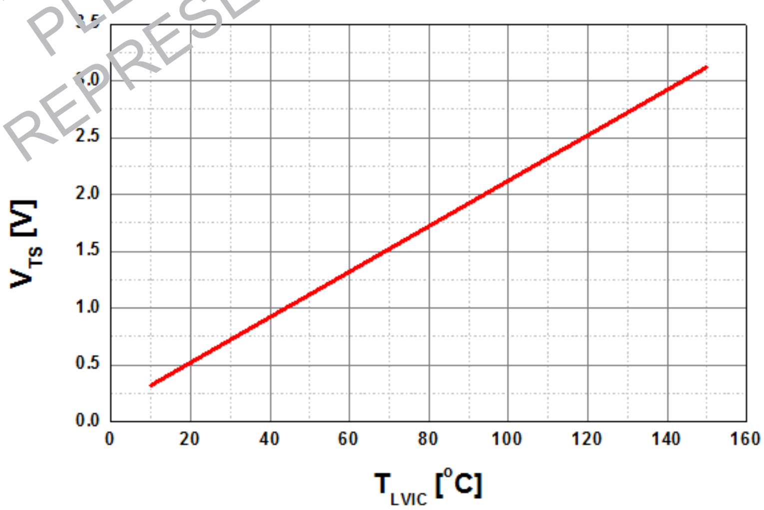


Figure 7. Temperature Profile of V_{TS} (Typical)

Bootstrap Diode Part

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage	I_F = 0.1 A, T_J = 25°C	-	2.5	-	V
t_{rr}	Reverse Recovery Time	I_F = 0.1 A, dI_F / dt = 50 A / µs, T_J = 25°C	-	80	-	ns

Control Part

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit
I_{QCCH}	Quiescent V_{CC} Supply Current	$V_{CC(H)}$ = 15 V, $IN_{(UH,VH,WH)}$ = 0 V	$V_{CC(H)}$ - COM	-	-	0.60	mA
I_{QCCL}		$V_{CC(L)}$ = 15 V, $IN_{(UL,VL,WL)}$ = 0 V	$V_{CC(L)}$ - COM	-	-	6.0	mA
I_{PCCH}	Operating V_{CC} Supply Current	$V_{CC(H)}$ = 15 V, f_{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input for High-Side	$V_{CC(H)}$ - COM	-	-	2.0	mA
I_{PCCL}		$V_{CC(L)}$ = 15V, f_{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input for Low-Side	$V_{CC(L)}$ - COM	-	-	10.0	mA
I_{QBS}	Quiescent V_{BS} Supply Current	V_{BS} = 15 V, $IN_{(UH,VH,WH)}$ = 0 V	$V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	-	-	0.50	mA
I_{PBS}	Operating V_{BS} Supply Current	V_{CC} = V_{BS} = 15 V, f_{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input for High-Side	$V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	-	-	2.0	mA
V_{FOH}	Fault Output Voltage	V_{CC} = 15 V, V_{SC} = 0 V, V_{FO} Circuit: 4.7 kΩ to 5 V Pull-up		4.5	-	-	V
V_{FOL}		V_{CC} = 15 V, V_{SC} = 1 V, V_{FO} Circuit: 4.7 kΩ to 5 V Pull-up		-	-	0.5	V
$V_{SC(ref)}$	Short Circuit Trip Level	V_{CC} = 15 V (Note 7)	C_{SC} - $COM_{(L)}$	0.45	0.50	0.55	V
UV_{CCD}	Supply Circuit Under-Voltage Protection	Detection Level		9.8	-	13.3	V
UV_{CCR}		Reset Level		10.3	-	13.8	V
UV_{BSD}		Detection Level		10.0	-	12.0	V
UV_{BSR}		Reset Level		10.5	-	12.5	V
t_{FOD}	Fault-Out Pulse Width			50	-	-	µs
V_{TS}	LVIC Temperature Sensing Voltage Output	$V_{CC(L)}$ = 15 V, T_{LVIC} = 25°C (Note 8) *See Figure 7*		540	640	740	mV
$V_{IN(ON)}$	ON Threshold Voltage	Applied between $IN_{(UH,VH,WH)}$ - COM, $IN_{(UL,VL,WL)}$ - COM		-	-	2.6	V
$V_{IN(OFF)}$	OFF Threshold Voltage			0.8	-	-	V

Note:

7. Short-circuit current protection is functioning only at the low-sides.

8. T_{LVIC} is the temperature of LVIC itself. V_{TS} is only for sensing temperature of LVIC and can not shutdown IGBTs automatically.

Recommended Operating Conditions

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ.	Max.	
V_{PN}	Supply Voltage	Applied between P - N_U, N_V, N_W	-	300	400	V
V_{CC}	Control Supply Voltage	Applied between $V_{CC(UH, VH, WH)}$ - COM, $V_{CC(L)}$ - COM	14.0	15	16.5	V
V_{BS}	High-Side Bias Voltage	Applied between $V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	13.0	15	18.5	V
dV_{CC} / dt, dV_{BS} / dt	Control Supply Variation		- 1	-	1	V / μs
t_{dead}	Blanking Time for Preventing Arm - Short	For Each Input Signal	2.0	-	-	μs
f_{PWM}	PWM Input Signal	-40°C ≤ T_C ≤ 125°C, -40°C ≤ T_J ≤ 150°C	-	-	20	kHz
V_{SEN}	Voltage for Current Sensing	Applied between N_U, N_V, N_W - COM (Including Surge Voltage)	- 4		4	V
T_J	Junction Temperature		- 40	-	150	°C

Note:

9. This product might not make response if input pulse width is less than the recommanded value.

Mechanical Characteristics and Ratings

Parameter	Conditions		Min.	Typ.	Max.	Unit
Mounting Torque	Mounting Screw: M3	Recommended 0.62 N•m	0.51	0.62	0.80	N•m
Device Flatness		See Figure 7	0	-	+150	μm
Weight			-	15.00	-	g

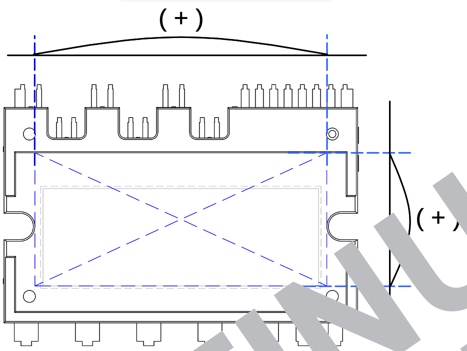


Figure 8. Flatness Measurement Position

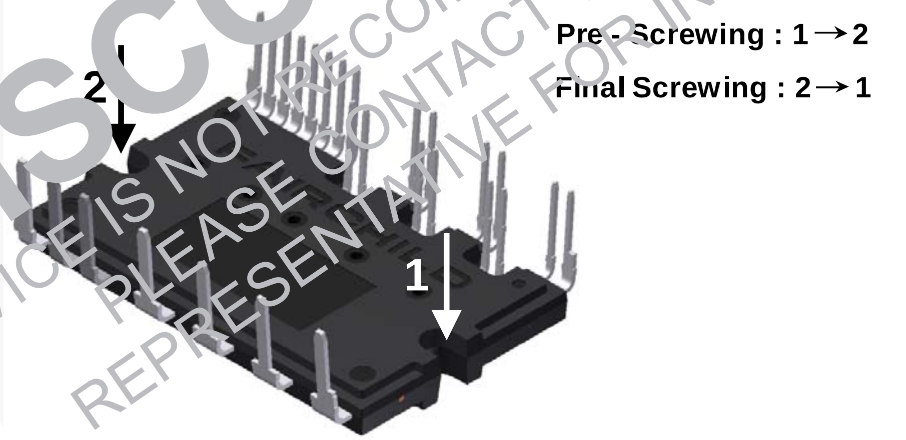


Figure 9. Mounting Screws Torque Order

Note:

10. Do not make over torque when mounting screws. Much mounting torque may cause DBC cracks, as well as bolts and Al heat-sink destruction.

11. Avoid one-sided tightening stress. Figure 9 shows the recommended torque order for mounting screws. Uneven mounting can cause the DBC substrate of package to be damaged. The pre-screwing torque is set to 20 ~ 30% of maximum torque rating.

Time Charts of SPMs Protective Function

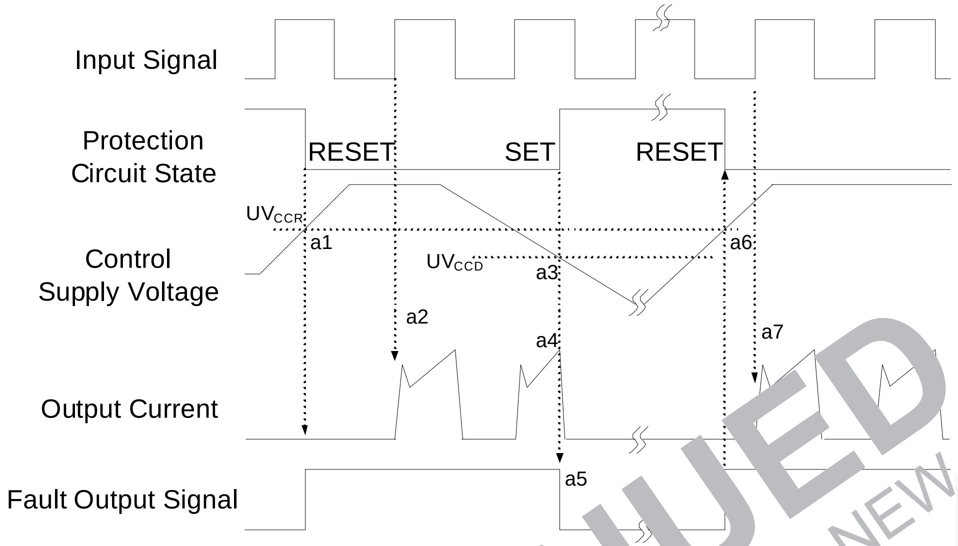


Figure 10. Under-Voltage Protection (Low-Side)

a1 : Control supply voltage rises: After the voltage rises UV_{CCR}, the circuits start to operate when next input is applied.

a2 : Normal operation: IGBT ON and carrying current.

a3 : Under voltage detection (UV_{CCD}).

a4 : IGBT OFF in spite of control input condition.

a5 : Fault output operation starts with a fixed pulse width.

a6 : Under voltage reset (UV_{CCR}).

a7 : Normal operation: IGBT ON and carrying current by triggering next signal from LOW to HIGH.

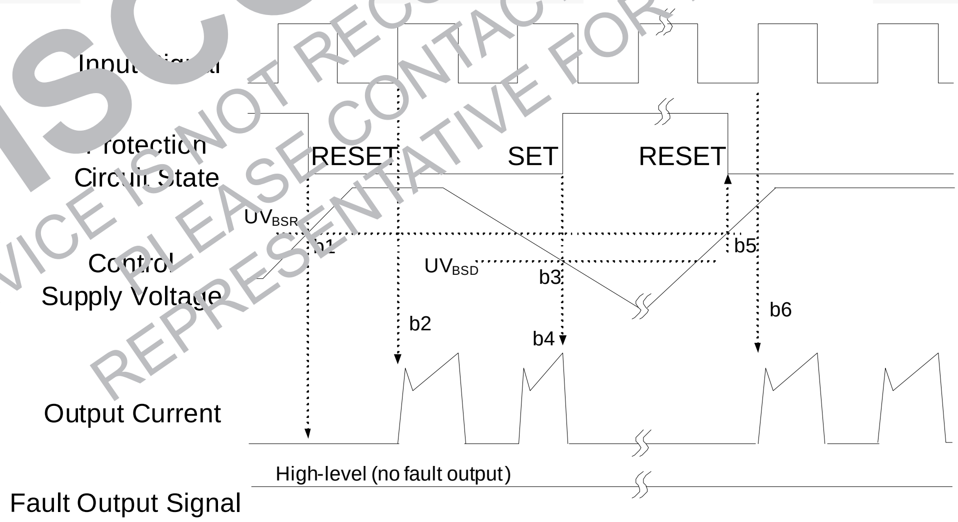


Figure 11. Under-Voltage Protection (High-Side)

b1 : Control supply voltage rises: After the voltage reaches UV_{BSR}, the circuits start to operate when next input is applied.

b2 : Normal operation: IGBT ON and carrying current.

b3 : Under voltage detection (UV_{BSD}).

b4 : IGBT OFF in spite of control input condition, but there is no fault output signal.

b5 : Under voltage reset (UV_{BSR}).

b6 : Normal operation: IGBT ON and carrying current by triggering next signal from LOW to HIGH.

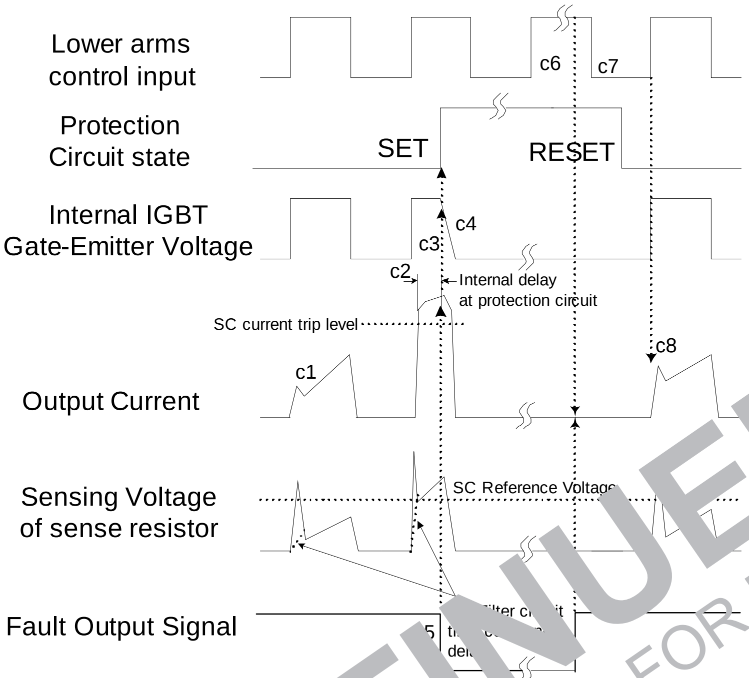


Figure 12. Short-Circuit Current Protection (Low-Side Operation only)

(with the external sense resistance and RC filter connection)

c1 : Normal operation: IGBT ON and carrying current.

c2 : Short circuit current detection (SC trigger).

c3 : All low-side IGBT's gate are hard interrupted.

c4 : All low-side IGBTs turn OFF.

c5 : Fault output operation starts with a fixed pulse width.

c6 : Input HIGH: IGBT ON state, but during the active period of fault output the IGBT doesn't turn ON.

c7 : Fault output operation finishes, but IGBT doesn't turn on until triggering next signal from LOW to HIGH.

c8 : Normal operation: IGBT ON and carrying current.

Input/Output Interface Circuit

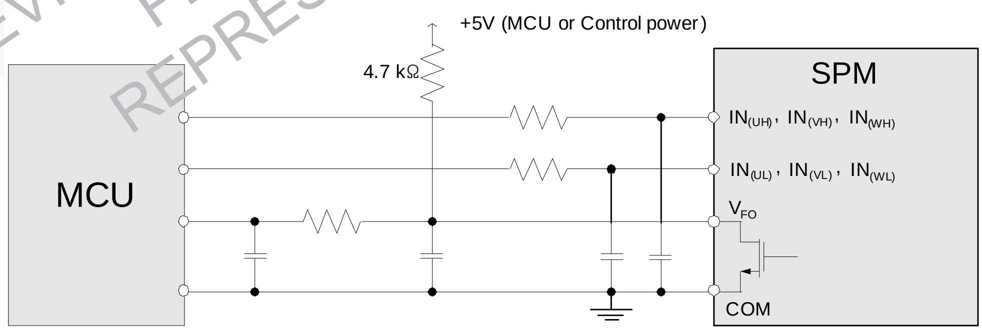


Figure 13. Recommended CPU I/O Interface Circuit

Note:

12. RC coupling at each input might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The input signal section of the Motion SPM 3 product integrates 5 kΩ (typ.) pull-down resistor. Therefore, when using an external filtering resistor, please pay attention to the signal voltage drop at input terminal.

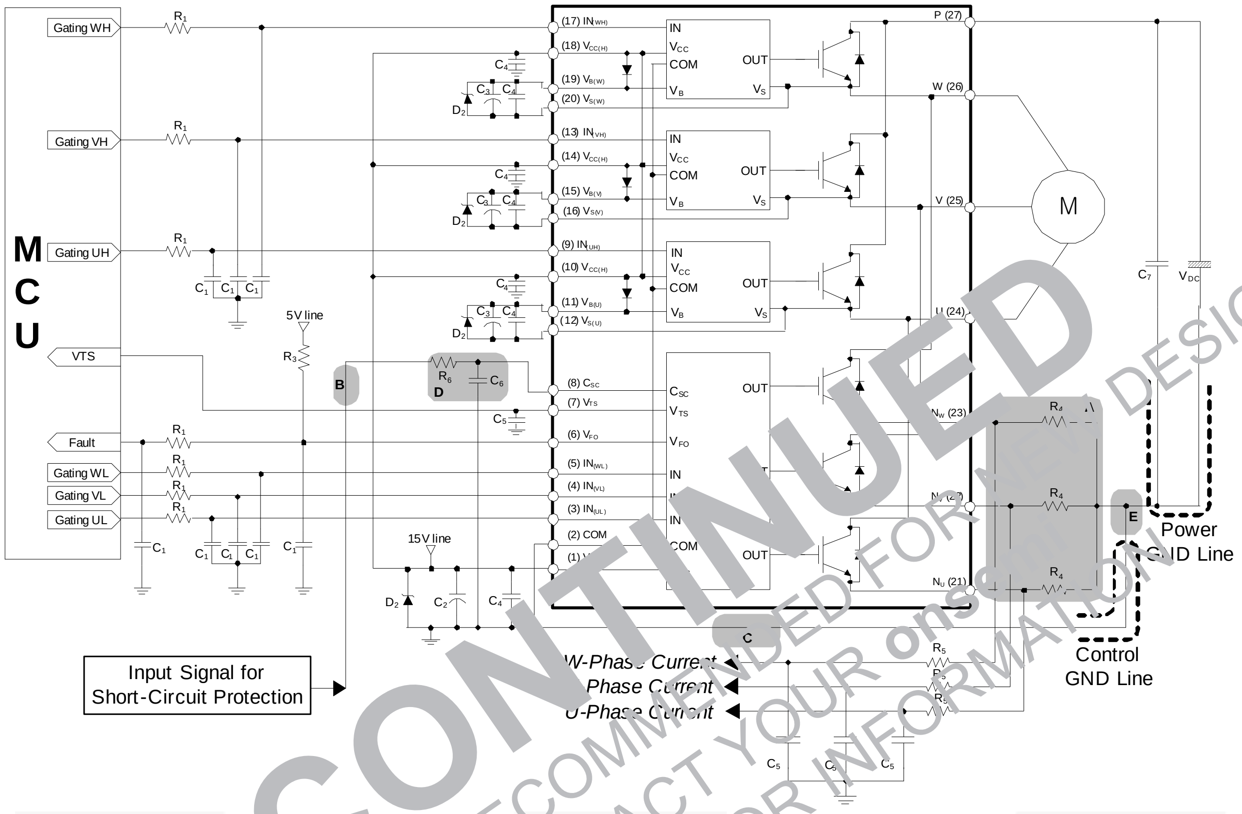
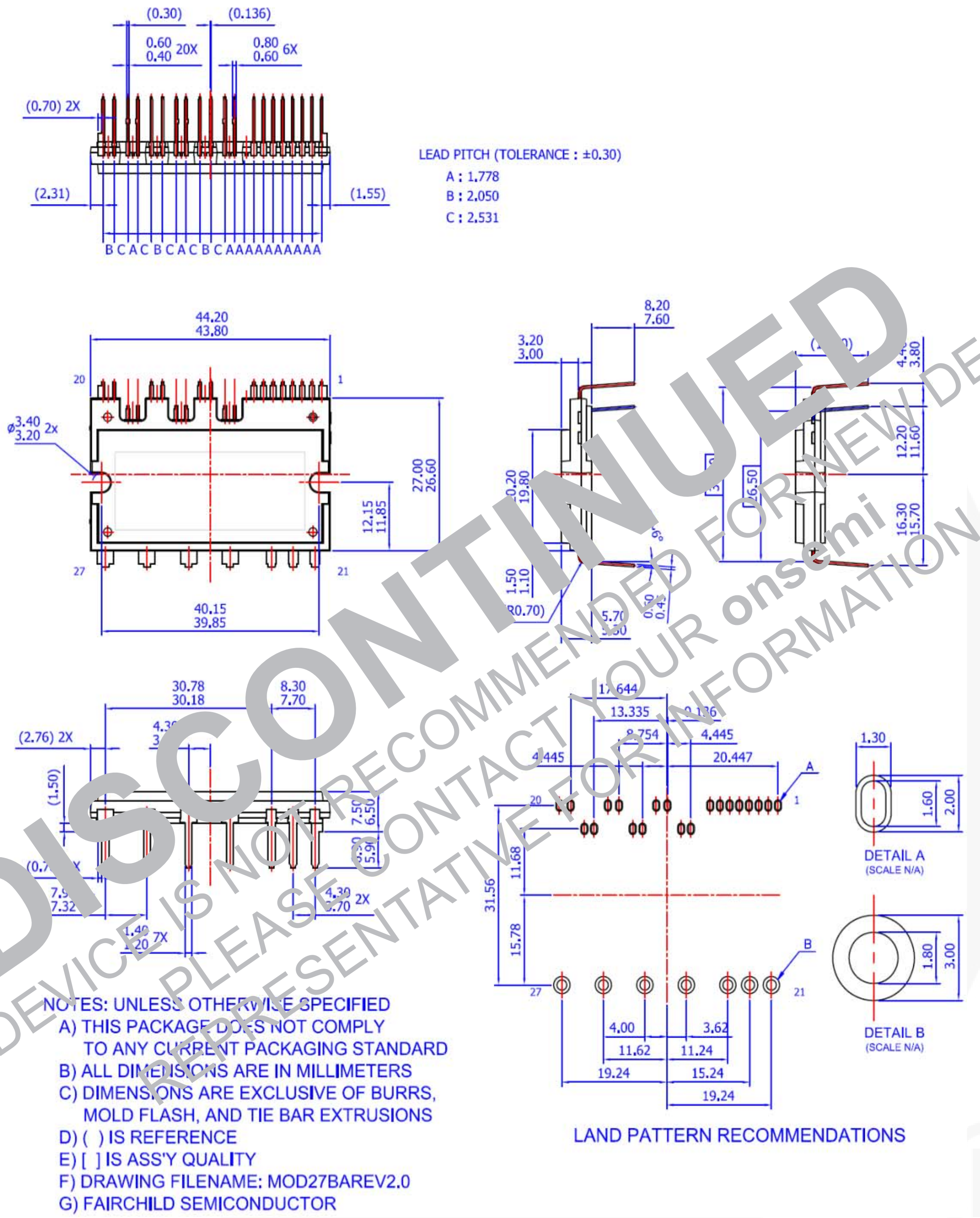


Figure 14. Typical Application Circuit

Note:

13. To avoid malfunction, the wiring of each input should be as short as possible. (less than 2 - 3 cm)
14. V_{FO} output is open-drain type. This signal line should be pulled up to the positive side of the MCU or control power supply with a resistor that makes I_{FO} up to 2 mA. Please refer to Figure 13.
15. Input signal is active-HIGH type. There is a 5 kΩ resistor inside the IC to pull-down each input signal line to GND. RC coupling circuits should be adopted for the prevention of input signal oscillation. R_1C_1 time constant should be selected in the range 50 ~ 150 ns. (Recommended R_1 = 100 Ω, C_1 = 1 nF)
16. Each wiring pattern inductance of A point should be minimized (Recommend less than 10nH). Use the shunt resistor R_4 of surface mounted (SMD) type to reduce wiring inductance. To prevent malfunction, wiring of point E should be connected to the terminal of the shunt resistor R_4 as close as possible.
17. To prevent errors of the protection function, the wiring of B, C, and D point should be as short as possible.
18. In the short-circuit protection circuit, please select the R_6C_6 time constant in the range 1.5 ~ 2 μs. Do enough evaluaiton on the real system because short-circuit protection time may vary wiring pattern layout and value of the R_6C_6 time constant.
19. Each capacitor should be mounted as close to the pins of the Motion SPM® 3 product as possible.
20. To prevent surge destruction, the wiring between the smoothing capacitor C_7 and the P & GND pins should be as short as possible. The use of a high-frequency non-inductive capacitor of around 0.1 ~ 0.22 μF between the P & GND pins is recommended.
21. Relays are used at almost every systems of electrical equipments at industrial application. In these cases, there should be sufficient distance between the CPU and the relays.
22. The zener diode or transient voltage suppressor should be adopted for the protection of ICs from the surge destruction between each pair of control supply terminals (Recommanded zener diode is 22 V / 1 W, which has the lower zener impedance characteristic than about 15Ω).
23. C_2 of around 7 times larger than bootstrap capacitor C_3 is recommended.
24. Please choose the electrolytic capacitor with good temperature characteristic in C_3. Also, choose 0.1 ~ 0.2 μF R-category ceramic capacitors with good temperature and frequency characteristics in C_4.

Detailed Package Outline Drawings (FSBB20CH60D)



Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or data on the drawing and contact a FairchildSemiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide therm and conditions, specifically the the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/dwg/MO/MOD27BA.pdf

FAIRCHILD.

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™
Awinda®
AX-CAP®*
BitSiC™
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficientMax™
ESBC™
®
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
FPS™

F-PFS™
FRFET®
Global Power Resource℠
GreenBridge™
Green FPS™
Green FPS™ e-Series™
G*max*™
GTO™
IntelliMAX™
ISOPLANAR™
Making Small Speakers Sound Louder and Better™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MicroPak2™
MillerDrive™
MotionMax™
MotionGrid®
MTi®
MTx®
MVN®
mWSaver®
OptoHiT™

®
PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
™
Saving our world, 1mW/W/kW at a time™
SignalWise™
SmartMax™
SMART START™
Solutions for Your Success™
SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS®
SyncFET™
Sync-Lock™

SYSTEM GENERAL®*
TinyBoost®
TinyBuck®
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TranSiC™
TriFault Detect™
TRUECURRENT®*
μSerDes™
μSerDes™
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™
Xsens™
仙童™

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT HTTP://WWW.FAIRCHILDSEMI.COM. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I71

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative